

## CLAIM AMENDMENTS

This listing of claims will replace all prior versions, and listings, of claims in the application:

### Listing of Claims:

1 (currently amended). A method for correcting local loading effects during etching of photomasks, which comprises the following steps:

determining a location-dependent density of mask structures resulting in a structure density, the determining step including:

forming a density function  $d(x,y)$  for determining the location dependent density of the mask structures;

determining a location-dependent strength of a loading effect with an aid of the structure density, the determining step including:

determining the location-dependent strength of the loading effect by a convolution of the density function with a Gauss function; and

determining location-dependent correction values for the mask structures using the location-dependent strength of the loading effect for compensating for the loading effect.

2 (original). The method according to claim 1, which further comprises determining the location-dependent density of the mask structures by analyzing a location-dependent bright field proportion of a mask surface that is to be generated.

3 (canceled).

4 (currently amended). The method according to claim 1 [[3]], which further comprises determining a location-dependent shift of edges of the mask structures with an aid of the location-dependent strength of the loading effect, the location-dependent correction values compensating for the location-dependent shift of the edges of the mask structures.

5 (original). The method according to claim 4, which further comprises using an equation for the location-dependent shift of the edges at point  $(x,y)$  on the mask surface being:

$$s(x,y) = m(t_0 - p_{\sigma}(x,y)),$$

whereby  $p_{\sigma}(x,y)$  is a density pseudo-function, and model parameters  $\sigma$ ,  $m$  and  $t_0$  are determined with an aid of measurements of uncorrected masks.

6 (original). The method according to claim 5, which further comprises calculating the density pseudo-function  $p_{\sigma}(x,y)$  by convolution of the density function  $d(x,y)$  of the mask structures with the Gauss function of a range  $\sigma$ .

7 (original). The method according to claim 5, which further comprises determining the location-dependent correction values by use of a correction function formed by inverting a sign of  $m$  from a function  $s(x,y)$ .

8 (original). The method according to claim 1, which further comprises:

partitioning a mask surface into subregions; and

assigning a location-dependent correction value to each of the subregions.

9 (original). The method according to claim 8, which further comprises creating a table for allocating the location-dependent correction value to each of the subregions.

10 (withdrawn and currently amended). A data processing system for configuring a layout of a mask, comprising:

means for reading design data representing a mask layout including mask structures to be fabricated and for processing the design data for correcting the mask layout represented by the design data, said means programmed to:

determine a location-dependent density of the mask structures resulting in a structure density;

form a density function  $d(x,y)$  for determining the location dependent density of the mask structures;

determine a location-dependent strength of a loading effect with an aid of the structure density; ~~and~~

determine the location-dependent strength of the loading effect by a convolution of the density function with a Gauss function; and

determine location-dependent correction values for the mask structures using the location-dependent strength of the loading effect for compensating for the loading effect.

11 (withdrawn and currently amended). A data processing system for configuring a layout of a mask, comprising:

means programmed to:

read first design data representing a mask layout including mask structures to be fabricated;

process the first design data for determining a location-dependent density of the mask structures resulting in a structure density, which includes forming a density function  $d(x,y)$  for determining the location dependent density of the mask structures;

determine a location-dependent strength of a loading effect with an aid of the structure density, which includes determining the location-dependent strength of the loading effect by a convolution of the density function with a Gauss function; and

determine location-dependent correction values for the mask structures with an aid of the location-dependent strength of the loading effect; and

generate second design data representing the mask layout, which has been corrected with the aid of the location-dependent correction values, of the mask that is to be fabricated.

12 (original). A computer program for configuring a layout of a mask and correcting mask structures: comprising:

computer executable instructions for carrying out the method according to claim 1.